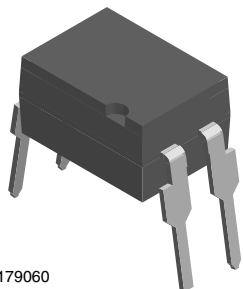
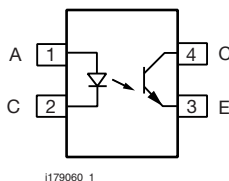


Optocoupler, Phototransistor Output, High Reliability, 5300 V_{RMS}

i179060



DESCRIPTION

The SFH615XXX features a large assortment of current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared emitting diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 package.

The coupling devices are designed for signal transmission between two electrically separated circuits.

The couplers are end-stackable with 2.54 mm lead spacing. Creepage and clearance distances of > 8 mm are achieved with option 6. This version complies with 60950 (DIN VDE 0805) for reinforced insulation up to operation voltage of 400 V_{RMS} or DC.

FEATURES

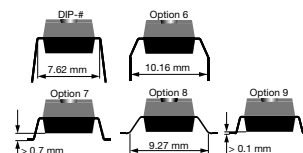
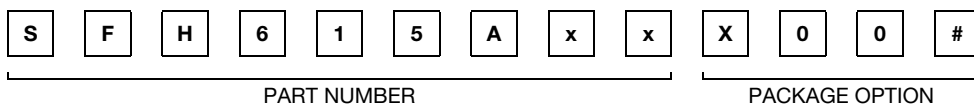
- Low CTR degradation
- Good CTR linearity depending on forward current
- Isolation test voltage, 5300 V_{RMS}
- High collector emitter voltage, V_{CEO} = 70 V
- Low saturation voltage
- Fast switching times
- Temperature stable
- Low coupling capacitance
- End stackable, 0.100" (2.54 mm) spacing
- High common mode interference immunity (unconnected base)
- Material categorization: for definitions of compliance please see www.vishay.com/doc299912

RoHS
COMPLIANT

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-5 (VDE 0884) available with option 1
- BSI IEC 60950; IEC 60065

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)						
	5 mA						
UL, VDE, BSI	50 to 600	80 to 260	200 to 600	200 to 400	100 to 600	100 to 300	50 to 150
DIP-4	SFH615AA	SFH615AB	SFH615ABL	SFH615ABM	SFH615AGB	SFH615AGR	SFH615AY
DIP-4, 400 mil, option 6	SFH615AA-X006	-	-	SFH615ABM-X006	-	SFH615AGR-X006	SFH615AY-X006
SMD-4, option 7	SFH615AA-X007	-	-	SFH615ABM-X007	SFH615AGB-X006	SFH615AGR-X007	-
SMD-4, option 8	-	-	-	-	-	-	SFH615AY-X008
SMD-4, option 9	-	-	-	-	SFH615AGB-X006	-	SFH615AY-X009

Note

- Additional options may be possible, please contact sales office.



ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
DC forward current		I_F	60	mA
Surge forward current	$t_p \leq 10\text{ ms}$	I_{FSM}	2.5	A
Power dissipation		P_{diss}	100	mW
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
	$t_p \leq 10\text{ ms}$	I_C	100	mA
Total power dissipation		P_{diss}	150	mW
COUPLER				
Isolation test voltage between emitter and detector		V_{ISO}	5300	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Isolation thickness between emitter and detector Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	≥ 175	
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{11}$	Ω
Storage temperature range		T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Ambient temperature range		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Soldering temperature ⁽¹⁾	max. 10 s, dip soldering distance to seating plane $\geq 1.5\text{ mm}$	T_{sld}	260	$^{\circ}\text{C}$

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽¹⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 60\text{ mA}$		V_F		1.25	1.65	V
Reverse current	$V_R = 6\text{ V}$		I_R		0.01	10	μA
Capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}$		C_O		13		pF
Thermal resistance			R_{thja}		750		K/W
OUTPUT							
Collector emitter capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}$		C_{CE}		5.2		pF
Thermal resistance			R_{thja}		500		K/W
Collector emitter saturation voltage	$I_F = 10\text{ mA}, I_C = 2.5\text{ mA}$		V_{CEsat}		0.25	0.4	V
Coupling capacitance			C_C		0.4		pF
COUPLER							
Collector emitter leakage current	$V_{CEO} = 10\text{ V}$	SFH615AA	I_{CEO}		10	100	nA
		SFH615AGB	I_{CEO}		10	100	nA
		SFH615AGR	I_{CEO}		10	100	nA
		SFH615ABM	I_{CEO}		10	100	nA
		SFH615ABL	I_{CEO}		10	100	nA
		SFH615AY	I_{CEO}		10	100	nA
		SFH615AB	I_{CEO}		10	100	nA

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

**CURRENT TRANSFER RATIO**

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$I_F = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$	SFH615AA	CTR	50		600	%
		SFH615AGB	CTR	100		600	%
		SFH615AGR	CTR	100		300	%
		SFH615ABM	CTR	200		400	%
		SFH615ABL	CTR	200		600	%
		SFH615AY	CTR	50		150	%
		SFH615AB	CTR	80		260	%

SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Turn-on time	$I_F = 5 \text{ mA}$	t_{on}		2		μs
Turn-off time	$I_F = 5 \text{ mA}$	t_{off}		25		μs

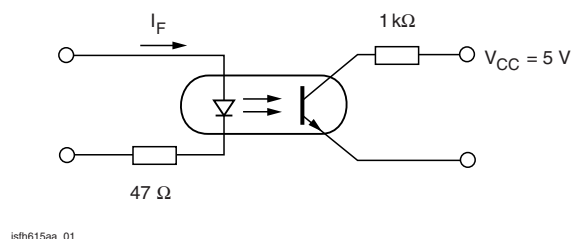
TYPICAL CHARACTERISTICS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

Fig. 1 - Switching Operation (with Saturation)

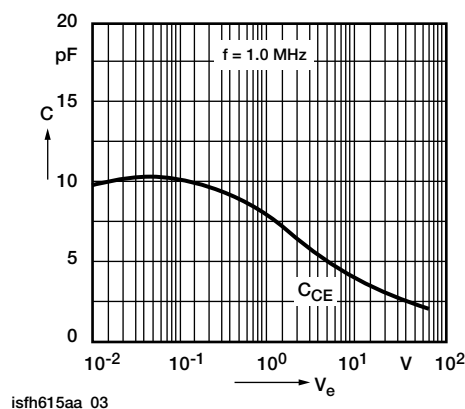


Fig. 3 - Transistor Capacitance (Typ.) vs. Collector Emitter Voltage

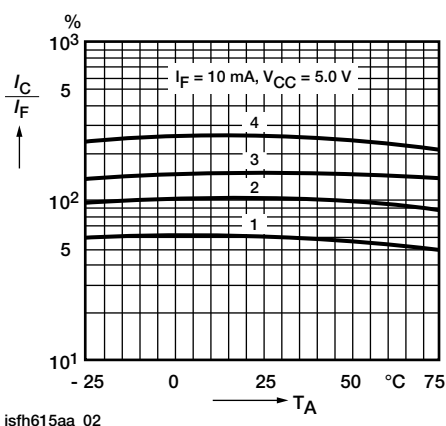


Fig. 2 - Current Transfer Ratio (Typ.) vs. Temperature

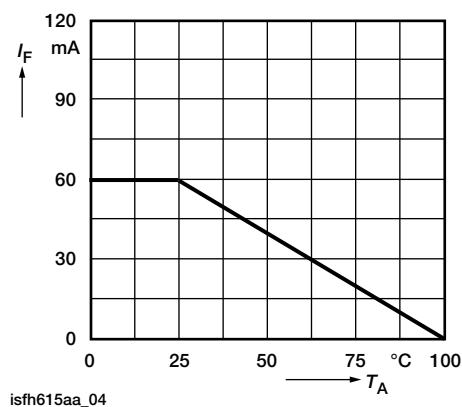


Fig. 4 - Permissible Diode Forward Current vs. Ambient Temperature

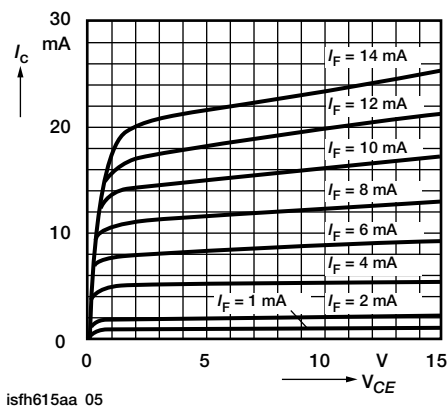


Fig. 5 - Output Characteristics (typ.) Collector Current vs. Collector Emitter Voltage

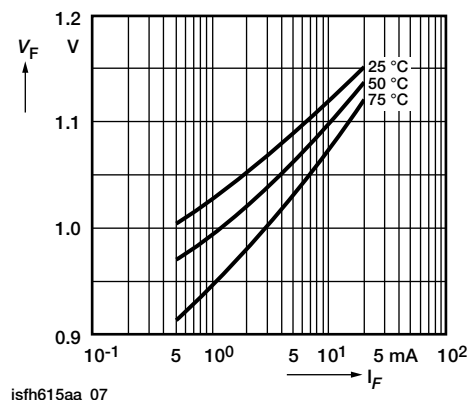


Fig. 7 - Diode Forward Voltage (typ.) vs. Forward Current

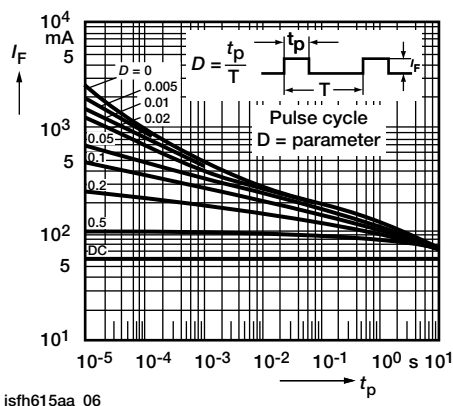


Fig. 6 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

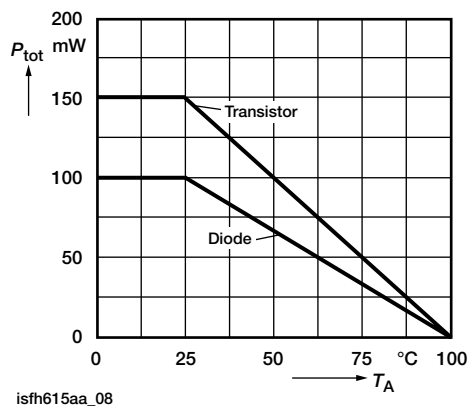
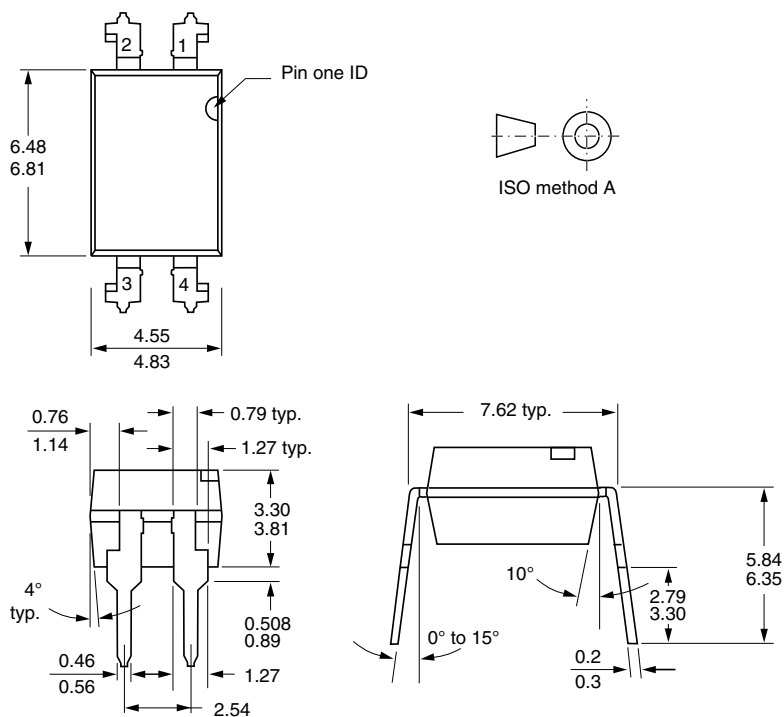


Fig. 8 - Permissible Power Dissipation vs. Temperature

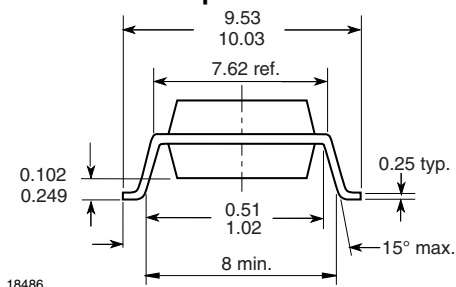


PACKAGE DIMENSIONS in inches (millimeters)



i178027

Option 9



18486



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